

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

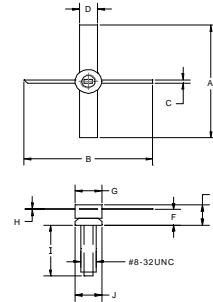
The ASI TVU0.5A is Designed for

**FEATURES:**

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- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

<b>I<sub>C</sub></b>	2.0 A
<b>V<sub>CB0</sub></b>	45 V
<b>V<sub>CEO</sub></b>	25 V
<b>V<sub>EBO</sub></b>	3.5 V
<b>P<sub>DISS</sub></b>	31.8 W @ T <sub>C</sub> = 25 °C
<b>T<sub>J</sub></b>	-65 °C to +200 °C
<b>T<sub>STG</sub></b>	-65 °C to +150 °C
<b>θ<sub>JC</sub></b>	33 °C/W

**PACKAGE STYLE .205 4L STUD**


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.976 / 24.800	1.000 / 25.4000
B	.976 / 24.800	1.000 / 25.4000
C	.028 / 0.700	.031 / 0.800
D	.138 / 3.500	
E	.161 / 4.100	.196 / 5.000
F	.098 / 2.500	.110 / 2.800
G	.200 / 5.100	.208 / 5.300
H	.004 / 0.100	.006 / 0.150
I	.425 / 10.800	.465 / 11.800
J	.200 / 5.100	2.05 / 5.200

**ORDER CODE: ASI10641**
**CHARACTERISTICS** T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>BV<sub>CB0</sub></b>	I <sub>C</sub> = 1.0 mA	45			<b>V</b>
<b>BV<sub>CEO</sub></b>	I <sub>C</sub> = 20 mA	24			<b>V</b>
<b>BV<sub>EBO</sub></b>	I <sub>E</sub> = 0.25 mA	3.5			<b>V</b>
<b>I<sub>CB0</sub></b>	V <sub>CB</sub> = 28 V			0.45	<b>mA</b>
<b>h<sub>FE</sub></b>	V <sub>CE</sub> = 5.0 V      I <sub>C</sub> = 100 mA	15		120	<b>---</b>
<b>P<sub>G</sub></b>	V <sub>CE</sub> = 20 V      I <sub>C</sub> = 150 mA      f = 860 MHz	9.5			<b>dB</b>
<b>IMD<sub>1</sub></b>	P <sub>OUT</sub> = 0.5 W	-58			<b>dBc</b>